



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: John T. Moore and David L. Chapek § Group Art Unit: 2811
Serial No.: 09/496,794 §
Filed: February 2, 2000 § Examiner: D. Owens
For: Trench Isolation for Semiconductor Devices § Atty. Dkt. No.: MICT-0005-D1-US

Commissioner for Patents
Washington DC 20231

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RESPONSE TO OFFICE ACTION DATED JUNE 29, 2001

Sir:

In response to the Office Action mailed June 29, 2001, the Applicants make the following amendments and remarks.

In the Claims

Please amend the claims as follows:

1. (Amended) A semiconductor structure having a trench, comprising:
a trench filler material that fills the trench;
at least a portion of a second material deposited on the trench filler material and the structure;
wherein the second material is annealed; and
wherein the etch rate of the second material is substantially similar to or less than the etch rate of the first material.

Please cancel claim 32.

Date of Deposit: 7/31/01
I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated above and is addressed to the Commissioner for Patents, Washington DC 20231.
Sharon V. Hart